In The Claims:

1. (original) A method of fabricating a shallow trench isolation (STI) structure, comprising the steps of:

providing a substrate;

forming a patterned mask layer over the substrate;

patterning the substrate using the mask layer as an etching mask to form a trench in the substrate;

performing a nitridation process to form a silicon nitride liner on the surface of the trench; and

depositing an insulating material over the trench and filling the trench with the insulating material.

- 2. (original) The method of claim 1, wherein the nitridation process comprises performing a furnace treatment.
- 3. (original) The method of claim 2, wherein the furnace treatment is carried out in an atmosphere of gaseous nitrogen.
- 4. (withdrawn) The method of claim 1, wherein the nitridation process comprises performing a rapid thermal treatment.
- 5. (withdrawn) The method of claim 4, wherein the rapid thermal treatment is carried out in an atmosphere of gaseous nitrogen.
- 6. (withdrawn) The method of claim 1, wherein the nitridation process comprises performing a plasma process.

- 7. (withdrawn) The method of claim 6, wherein the plasma process comprises performing a nitrogen plasma treatment.
- 8. (original) The method of claim 1, further comprising forming a liner oxide layer over the substrate,, wherein the formation of the liner oxide layer and the nitridation process for forming the silicon nitride liner are performed in-situ.
- 9. (original) The method of claim 8, wherein the step of forming the liner oxide layer comprises performing a thermal oxidation and integrating the thermal oxidation process with the nitridation process by introducing gaseous nitrogen mid-way through the thermal treatment.

Claims 10-11 (canceled)

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No new matter has been added to the application by the amendments made to the claims.

Respectfully submitted,

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